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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74LV4053A

Triple 2-channel Analog Multiplexer / Demultiplexer



ADE-205-284A (Z)

2nd. Edition
Jul. 2001

Description

The HD74LV4053A handles both analog and digital signals, and enables signals of either type with amplitudes of up to 5.5 V (peak) to be transmitted in either direction (at $V_{CC} = 0$ V to 5.5 V).

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

Features

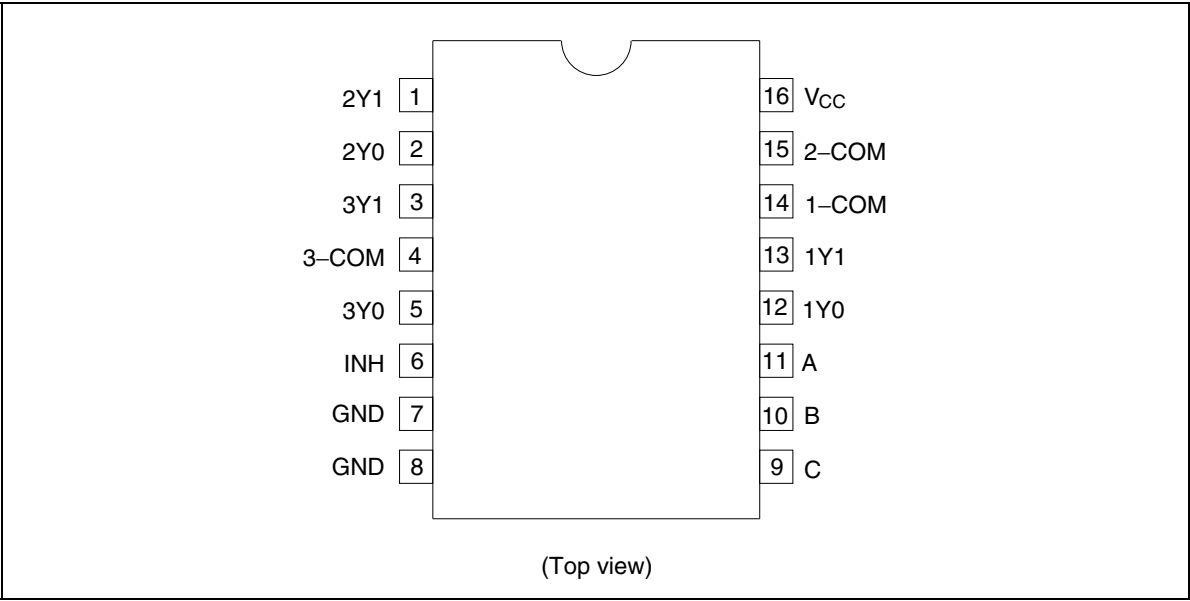
- $V_{CC} = 2.0$ V to 5.5 V operation
- All control inputs V_{IH} (Max.) = 5.5 V (@ $V_{CC} = 0$ V to 5.5 V)

Function Table

Inputs				On Channel
INH	C	B	A	
L	L	L	L	1Y0, 2Y0, 3Y0
L	L	L	H	1Y1, 2Y0, 3Y0
L	L	H	L	1Y0, 2Y1, 3Y0
L	L	H	H	1Y1, 2Y1, 3Y0
L	H	L	L	1Y0, 2Y0, 3Y1
L	H	L	H	1Y1, 2Y0, 3Y1
L	H	H	L	1Y0, 2Y1, 3Y1
L	H	H	H	1Y1, 2Y1, 3Y1
H	X	X	X	NONE

Note: H: High level
L: Low level
X: Immaterial

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V_{CC}	-0.5 to 7.0	V	
Input voltage range* ¹	V_I	-0.5 to 7.0	V	
Output voltage range* ^{1, 2}	V_O	-0.5 to $V_{CC} + 0.5$	V	Output: H or L
Input clamp current	I_{IK}	-20	mA	$V_I < 0$
Output clamp current	I_{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	±25	mA	$V_O = 0$ to V_{CC}
Continuous current through V_{CC} or GND	I_{CC} or I_{GND}	±50	mA	
Maximum power dissipation at $T_a = 25^\circ\text{C}$ (in still air)* ³	P_T	785	mW	SOP
		500		TSSOP
Storage temperature	T_{stg}	-65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded even if the input and output clamp-current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

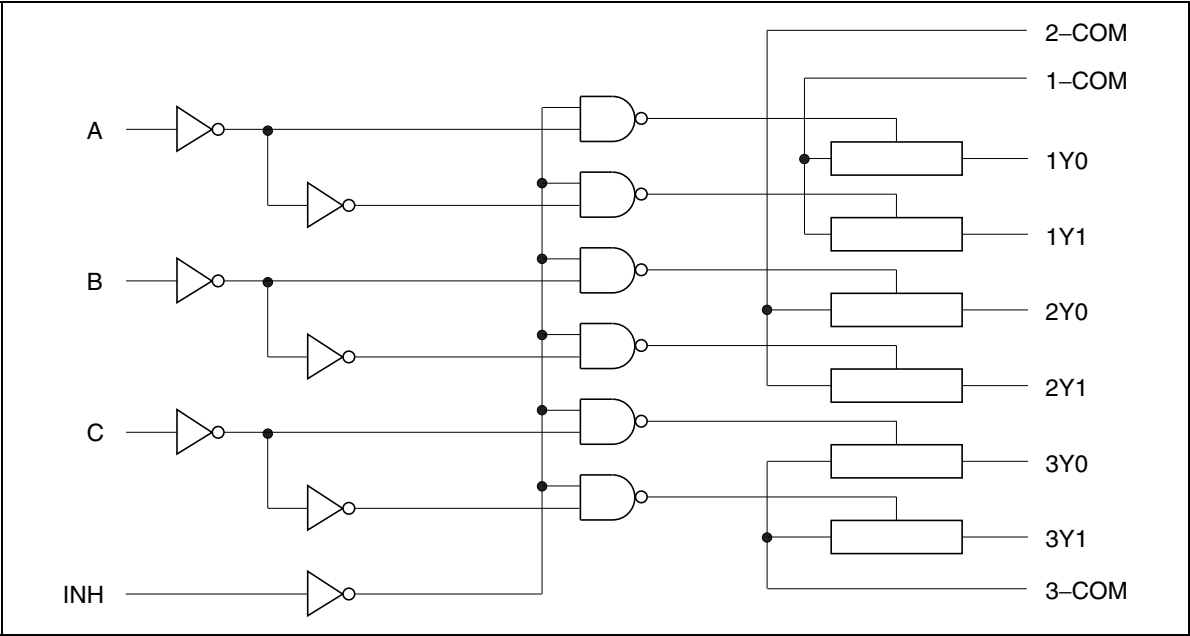
Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V_{CC}	2.0* ¹	5.5	V	
Input voltage range	V_I	0	5.5	V	
Output voltage range	V_{IO}	0	V_{CC}	V	
Input transition rise or fall rate	$\Delta t / \Delta v$	0	200	ns/V	$V_{CC} = 2.3$ to 2.7 V
		0	100		$V_{CC} = 3.0$ to 3.6 V
		0	20		$V_{CC} = 4.5$ to 5.5 V
Operating free-air temperature	T_a	-40	85	°C	

Notes: Unused or floating control inputs must be held high or low.

1. With the supply voltage at or around 2 V, the analog switch on-state resistance loses linearity significantly. It is recommended that only digital signals be transmitted at these low supply voltages.

Logic Diagram



DC Electrical Characteristics

Item	Symbol	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \text{ to } 85^{\circ}\text{C}$		Unit	Test Conditions
			Min	Typ	Max	Min	Max		
Input voltage	V_{IH}	2.0	—	—	—	1.5	—	V	Control input only
		2.3 to 2.7	—	—	—	$V_{CC} \times 0.7$	—		
		3.0 to 3.6	—	—	—	$V_{CC} \times 0.7$	—		
		4.5 to 5.5	—	—	—	$V_{CC} \times 0.7$	—		
	V_{IL}	2.0	—	—	—	—	0.5		
		2.3 to 2.7	—	—	—	—	$V_{CC} \times 0.3$		
		3.0 to 3.6	—	—	—	—	$V_{CC} \times 0.3$		
		4.5 to 5.5	—	—	—	—	$V_{CC} \times 0.3$		
On-state switch resistance	R_{ON}	2.3	—	60	180	—	225	Ω	$V_{IN} = V_{CC}$ or GND $V_{INH} = V_{IL}$ $I_T = 2 \text{ mA}$
		3.0	—	50	150	—	190		
		4.5	—	40	75	—	100		
Peak on resistance	$R_{ON(P)}$	2.3	—	200	500	—	600	Ω	$V_{IN} = V_{CC}$ to GND $V_{INH} = V_{IL}$ $I_T = 2 \text{ mA}$
		3.0	—	90	180	—	225		
		4.5	—	50	100	—	125		
Difference of on-state resistance between switches	ΔR_{ON}	2.3	—	20	30	—	40	Ω	$V_{IN} = V_{CC}$ to GND $V_{INH} = V_{IL}$ $I_T = 2 \text{ mA}$
		3.0	—	10	20	—	30		
		4.5	—	7	15	—	20		
Off-state switch leakage current	I_s (OFF)	5.5	—	—	± 0.1	—	± 1.0	μA	$V_{IN} = V_{CC}$, $V_{OUT} = \text{GND}$ or $V_{IN} = \text{GND}$, $V_O = V_{CC}$, $V_{INH} = V_{IH}$
On-state switch leakage current	I_s (ON)	5.5	—	—	± 0.1	—	± 1.0	μA	$V_{IN} = V_{CC}$ or GND $V_{INH} = V_{IL}$
Input current	I_{IN}	0 to 5.5	—	—	± 0.1	—	± 1.0	μA	$V_{IN} = 5.5 \text{ V}$ or GND
Quiescent supply current	I_{CC}	5.5	—	—	—	—	20	μA	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max use the appropriate values under recommended operating conditions.

Switching Characteristics

V_{CC} = 2.5 ± 0.2 V

Item	Symbol	Ta = 25°C			Ta = −40 to 85°C		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max	Min	Max				
Propagation delay time	t _{PLH}	—	2.5	10.0	—	16.0	ns	C _L = 15 pF	COM or Yn	Yn or COM
	t _{PHL}	—	5.0	12.0	—	18.0		C _L = 50 pF		
Enable time	t _{ZH}	—	7.0	18.0	—	23.0	ns	R _L = 1 kΩ C _L = 15 pF	INH	COM or Yn
	t _{ZL}	—	9.0	28.0	—	35.0		C _L = 50 pF		
Disable time	t _{HZ}	—	9.0	18.0	—	23.0	ns	R _L = 1 kΩ C _L = 15 pF	INH	COM or Yn
	t _{LZ}	—	13.0	28.0	—	35.0		C _L = 50 pF		

V_{CC} = 3.3 ± 0.3 V

Item	Symbol	Ta = 25°C			Ta = −40 to 85°C		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max	Min	Max				
Propagation delay time	t _{PLH}	—	2.0	6.0	—	10.0	ns	C _L = 15 pF	COM or Yn	Yn or COM
	t _{PHL}	—	4.0	9.0	—	12.0		C _L = 50 pF		
Enable time	t _{ZH}	—	5.0	12.0	—	15.0	ns	R _L = 1 kΩ C _L = 15 pF	INH	COM or Yn
	t _{ZL}	—	7.0	20.0	—	25.0		C _L = 50 pF		
Disable time	t _{HZ}	—	7.0	12.0	—	15.0	ns	R _L = 1 kΩ C _L = 15 pF	INH	COM or Yn
	t _{LZ}	—	10.0	20.0	—	25.0		C _L = 50 pF		

Switching Characteristics (cont)

$$V_{CC} = 5.0 \pm 0.5 \text{ V}$$

Item	Symbol	Ta = 25°C			Ta = -40 to 85°C		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max	Min	Max				
Propagation delay time	t_{PLH}	—	1.5	4.0	—	7.0	ns	$C_L = 15 \text{ pF}$	COM or Yn	Yn or COM
	t_{PHL}	—	3.0	6.0	—	8.0		$C_L = 50 \text{ pF}$		
Enable time	t_{ZH}	—	4.0	8.0	—	10.0	ns	$R_L = 1 \text{ k}\Omega$ $C_L = 15 \text{ pF}$	INH	COM or Yn
	t_{ZL}	—	5.0	14.0	—	18.0		$C_L = 50 \text{ pF}$		
Disable time	t_{HZ}	—	5.0	8.0	—	10.0	ns	$R_L = 1 \text{ k}\Omega$ $C_L = 15 \text{ pF}$	INH	COM or Yn
	t_{LZ}	—	8.0	14.0	—	18.0		$C_L = 50 \text{ pF}$		

Switching Characteristics (cont)**Ta = 25°C**

Item	Symbol	V _{cc} (V)	Min	Typ	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Control input capacitance	C _{ic}	—	—	4.5	—	pF			
Common terminal capacitance	C _{is}	—	—	12.5	—	pF			
Switch terminal capacitance	C _{io}	—	—	7.0	—	pF			
Feedthrough capacitance	C _T	—	—	0.5	—	pF			
Power dissipation capacitance	C _{PD}	—	—	9.0	—	pF			
Frequency response (Switch ON)		2.3	—	30.0	—	MHz	C _L = 50 pF, R _L = 600 Ω Adjust f _{in} voltage to obtain 0 dBm at output when f _{in} is 1 MHz (sine wave). Increase f _{in} frequency until the dB-meter reads -3 dBm. 20 log (V _o /V _i) = -3 dBm	COM or Yn	Yn or COM
		3.0	—	35.0	—				
		4.5	—	50.0	—				
Crosstalk (Between any switches)		2.3	—	-45.0	—	dB	C _L = 50 pF, R _L = 600 Ω Adjust f _{in} voltage to obtain 0 dBm at input when f _{in} is 1 MHz (sine wave).	COM	Yn
		3.0	—	-45.0	—				
		4.5	—	-45.0	—				
Crosstalk (Control input to signal output)		2.3	—	20.0	—	mV	C _L = 50 pF, R _L = 600 Ω Adjust R _L value to obtain 0 A at I _{IN/OUT} when f _{in} is 1 MHz (square wave).	INH	COM or Yn
		3.0	—	35.0	—				
		4.5	—	65.0	—				

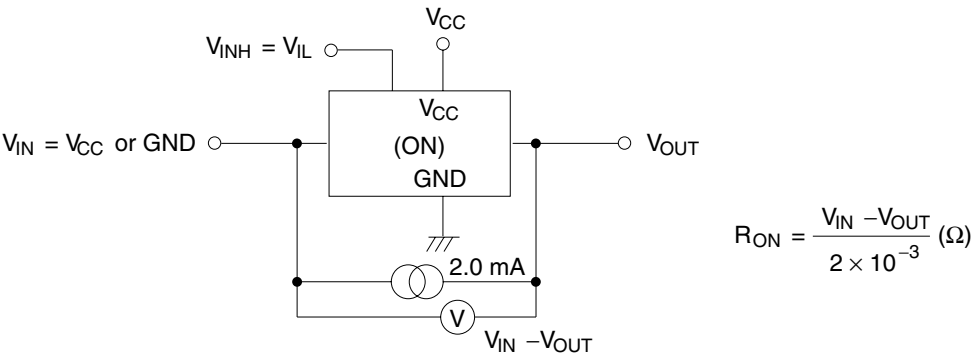
Switching Characteristics (cont)

Ta = 25°C

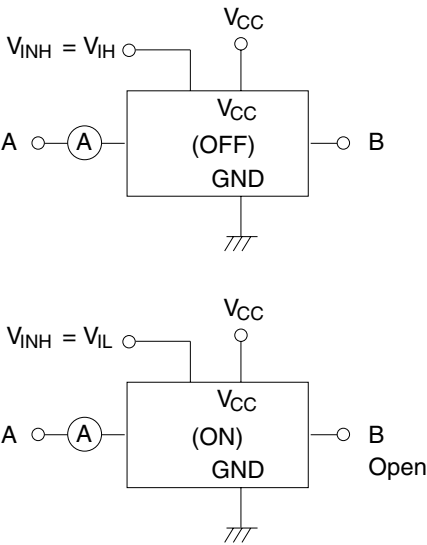
Item	Symbol	V _{cc} (V)	Min	Typ	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Feedthrough attenuation (Switch OFF)		2.3	—	−45	—	dB	C _L = 50 pF, R _L = 600 Ω Adjust f _{in} voltage to obtain 0 dBm at input when f _{in} is 1 MHz (sine wave).	COM or Yn	Yn or COM
		3.0	—	−45	—				
		4.5	—	−45	—				
Sine-wave distortion		2.3	—	0.1	—	%	C _L = 50 pF, R _L = 10 kΩ f _{in} = 1 kHz (sine wave) V _I = 2 V _{P-P} , V _{CC} = 2.3 V V _I = 2.5 V _{P-P} , V _{CC} = 3.0 V V _I = 4 V _{P-P} , V _{CC} = 4.5 V	COM or Yn	Yn or COM
		3.0	—	0.1	—				
		4.5	—	0.1	—				

Test Circuits

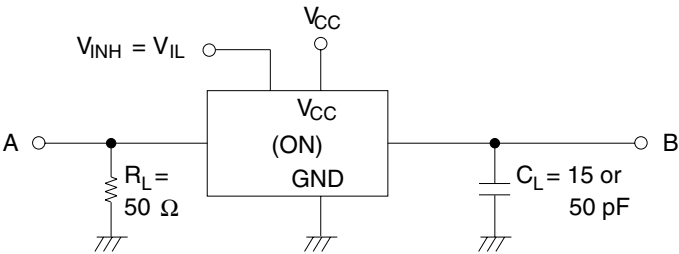
R_{ON}: On-state switch resistance



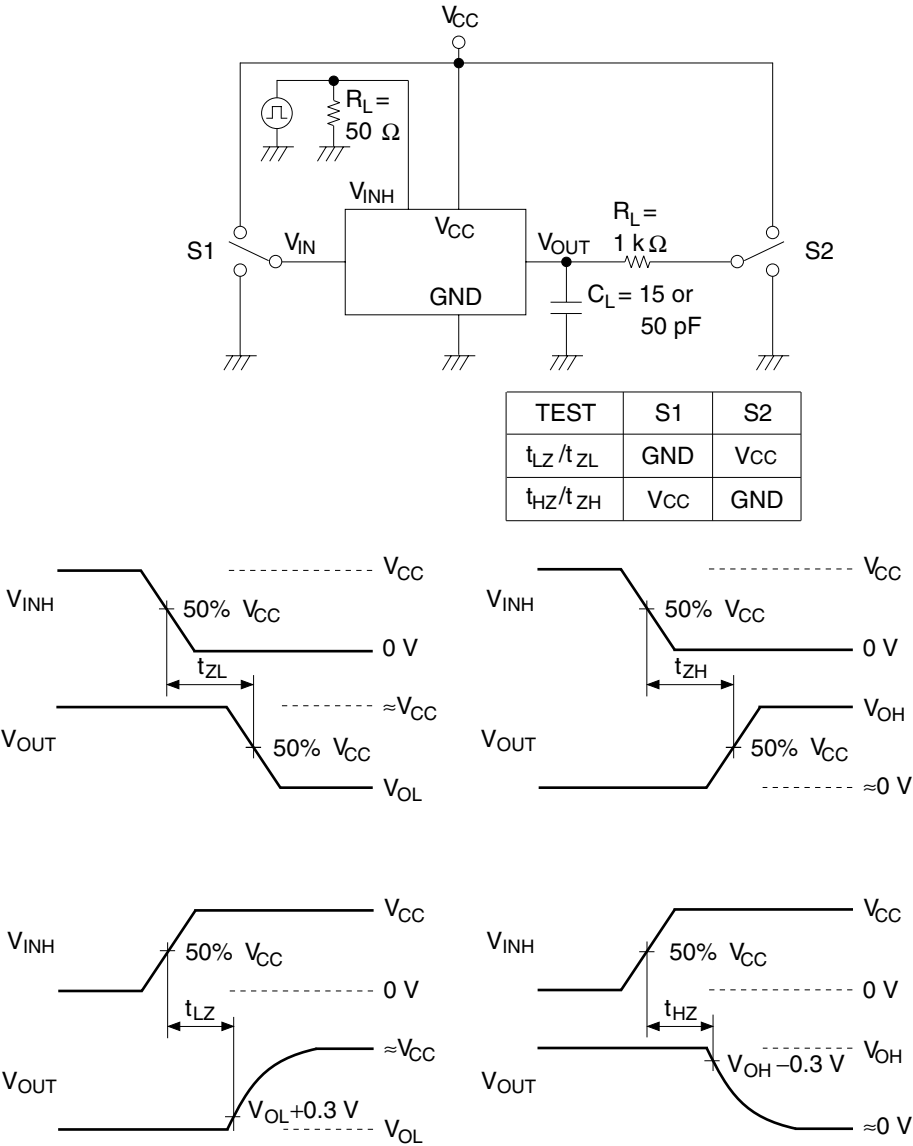
I_s (OFF): Off-state switch leakage current, I_s (ON): On-state switch leakage current



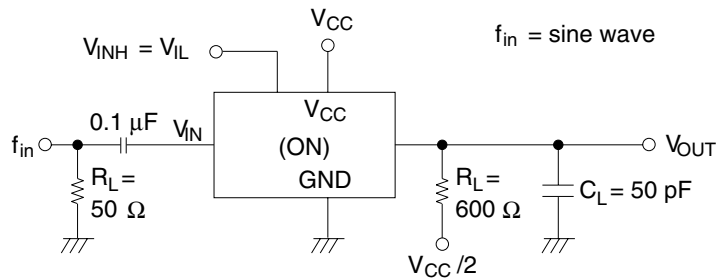
t_{PLH} , t_{PHL} : Propagation delay time (from switch input to switch output)



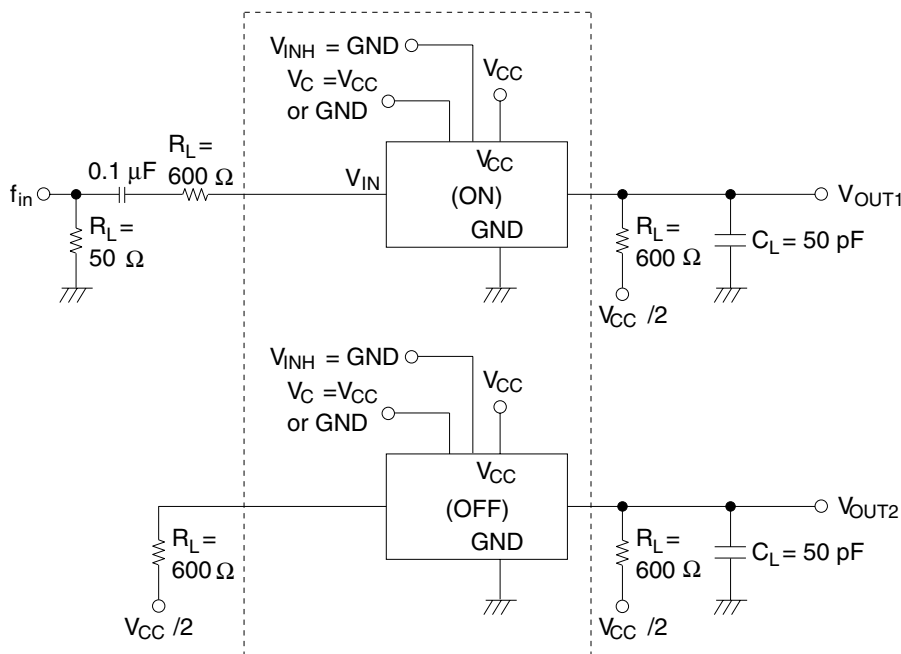
Switching time



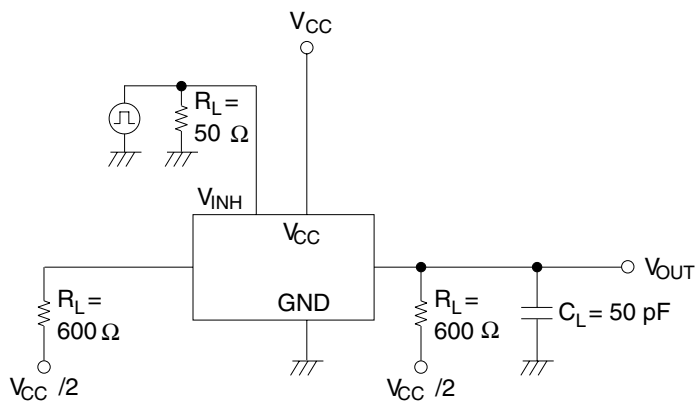
Frequency response (Switch ON)



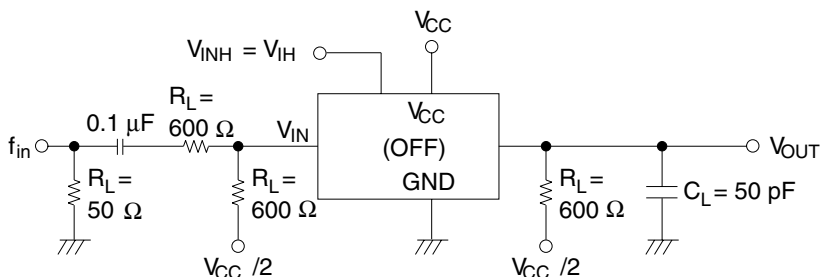
Crosstalk (Between any switches)



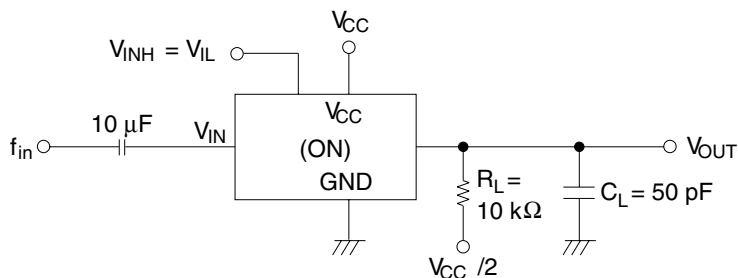
Crosstalk (Control input to signal output)



Feedthrough attenuation (Switch OFF)

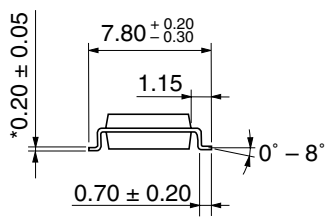
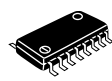
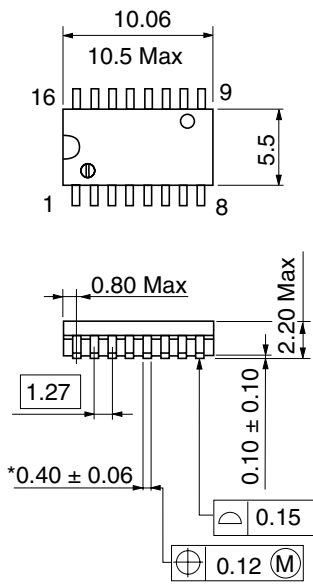


Sine-wave distortion



Package Dimensions

As of July, 2001
Unit: mm

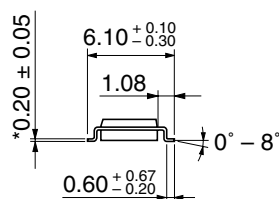
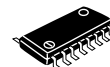
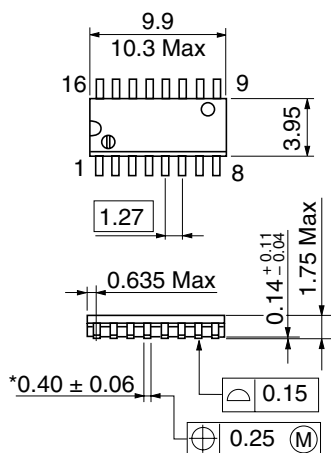


*Pd plating

Hitachi Code	FP-16DAV
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.24 g

As of July, 2001

Unit: mm

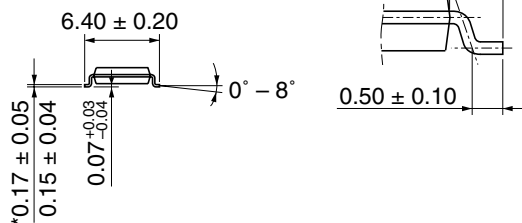
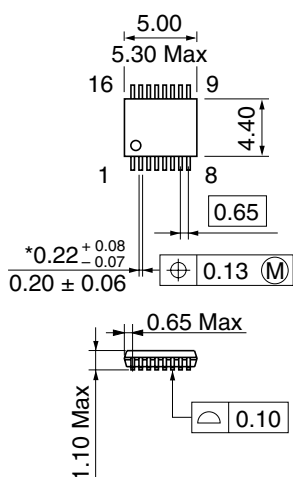


*Pd plating

Hitachi Code	FP-16DNV
JEDEC	Conforms
JEITA	Conforms
Mass (reference value)	0.15 g

As of July, 2001

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-16DA
JEDEC	—
JEITA	—
Mass (reference value)	0.05 g

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